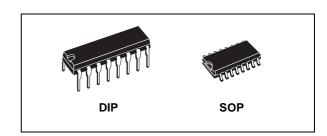




QUAD AND/OR SELECT GATE

- MEDIUM-SPEED OPERATION t_{PD} = 60ns (Typ.) at V_{DD} = 10V
- QUIESCENT CURRENT SPECIFIED UP TO
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



ORDER CODES

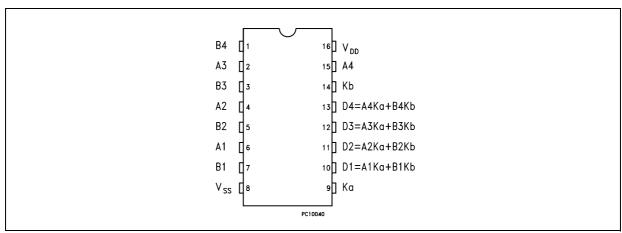
PACKAGE	TUBE	T&R
DIP	HCF4019BEY	
SOP	HCF4019BM1	HCF4019M013TR

DESCRIPTION

The HCF4019B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. The HCF4019B types are comprised of four AND/OR select gate configurations, each consisting of two 2 input AND gates driving a single 2-input OR

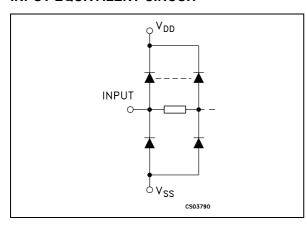
gate. Selection is accomplished by control bits K_a and K_b . In addition to selection of either channel A or channel B information, the control bits can be applied simultaneously to accomplish the logical A+B function.

PIN CONNECTION

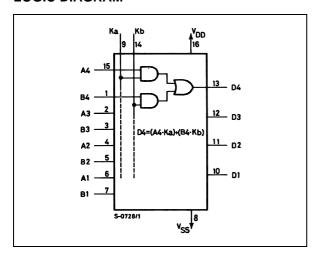


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INPUT EQUIVALENT CIRCUIT



LOGIC DIAGRAM



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
6, 4, 2, 15	A1 to A4	Data Inputs
7, 5, 3, 1	B1 to B4	Data inputs
10, 11,12, 13	D1 to D4	Data Outputs
9, 14	K _a , K _b	Control bits
8	V_{SS}	Negative Supply Voltage
16	V_{DD}	Positive Supply Voltage

TRUTH TABLE

CON	CONTROL		INPUTS				
Ka	Kb	A1 to A4	B1 to B4	D1 to D4			
Н	Х	Н	Х	Н			
Н	Х	L	Х	L			
Х	Н	Х	Н	Н			
Х	Н	Х	L	L			
L	L	Х	Х	L			

X : Don"t Care

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	-0.5 to +22	V
V _I	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 20	V
VI	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	ç

DC SPECIFICATIONS

			Test Con	dition					Value				
Symbol	Parameter	Vı	v _o	ΙΙ _Ο Ι	V _{DD}	Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)	(V)	(μ A)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
ΙL	Quiescent Current	0/5			5		0.02	1		30		30	
		0/10			10		0.02	2		60		60	^
		0/15			15		0.02	4		120		120	μΑ
		0/20			20		0.04	20		600		600	
V_{OH}	High Level Output	0/5		<1	5	4.95			4.95		4.95		
	Voltage	0/10		<1	10	9.95			9.95		9.95		V
		0/15		<1	15	14.95			14.95		14.95		
V_{OL}	Low Level Output	5/0		<1	5		0.05			0.05		0.05	
	Voltage	10/0		<1	10		0.05			0.05		0.05	V
		15/0		<1	15		0.05			0.05		0.05	
V_{IH}	High Level Input		0.5/4.5	<1	5	3.5			3.5		3.5		
	Voltage		1/9	<1	10	7			7		7		V
			1.5/13.5	<1	15	11			11		11		
V_{IL}	Low Level Input		4.5/0.5	<1	5			1.5		1.5		1.5	
	Voltage		9/1	<1	10			3		3		3	V
			13.5/1.5	<1	15			4		4		4	
I _{OH}	Output Drive	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		
	Current	0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		mA
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		ША
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
l _{OL}	Output Sink	0/5	0.4	<1	5	0.44	1		0.36		0.36		
	Current	0/10	0.5	<1	10	1.1	2.6		0.9		0.9		mΑ
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
l _l	Input Leakage Current	0/18	Any In	put	18		±10 ⁻⁵	±0.1		±1		±1	μΑ
CI	Input Capacitance		Any In	put			5	7.5					рF

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD} =5V, 2V min. with V_{DD} =10V, 2.5V min. with V_{DD} =15V

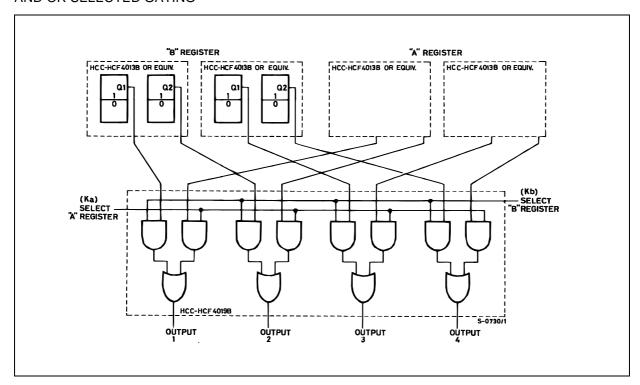
$\textbf{DYNAMIC ELECTRICAL CHARACTERISTICS} \; (T_{amb} = 25^{\circ}C, \;\; C_{L} = 50 pF, \; R_{L} = 200 K\Omega, \;\; t_{f} = t_{f} = 20 \; ns)$

Cumbal	Davamatar		Test Condition	'	/alue (*	·)	Unit
Symbol	Parameter	V _{DD} (V)		Min.	Тур.	Max.	
t _{PLH} t _{PHL}	Propagation Delay Time	5			150	300	
		10			60	120	ns
		15			50	100	
t _{TLH} t _{THL}	Output Transition Time	5			100	200	
		10			50	100	ns
		15			40	80	

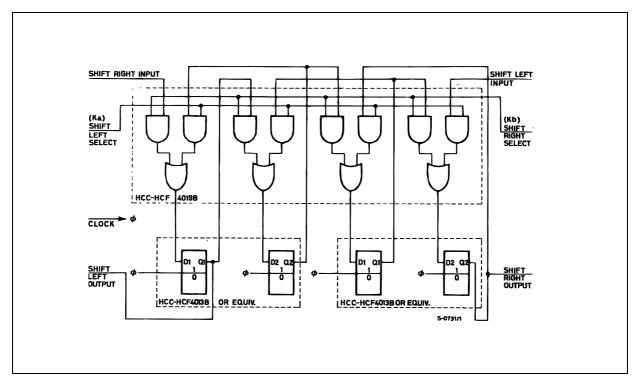
(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C.

TYPICAL APPLICATIONS

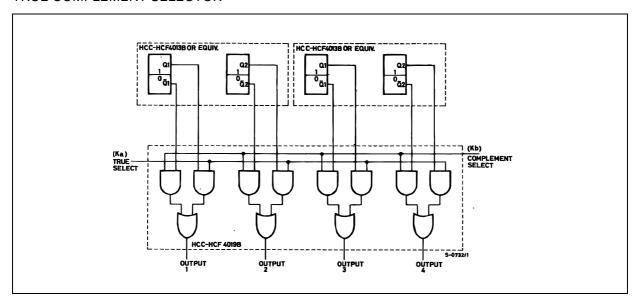
AND OR SELECTED GATING



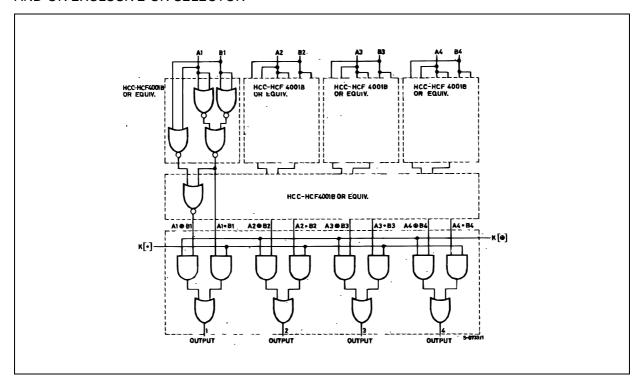
SHIFT LEFT SHIFT RIGHT REGISTER



TRUE COMPLEMENT SELECTOR



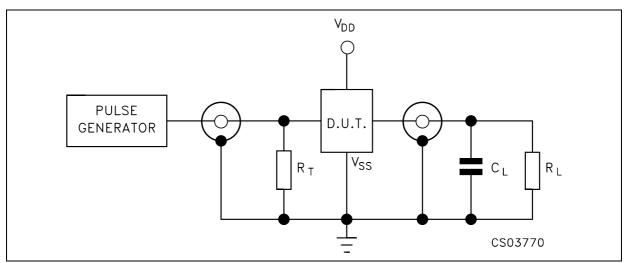
AND-OR EXCLUSIVE OR SELECTOR



TRUTH TABLE

K[*]	K[⊕]	OUT
L	L	L
Н	L	A-B
L	Н	A⊕B
Н	Н	A+B

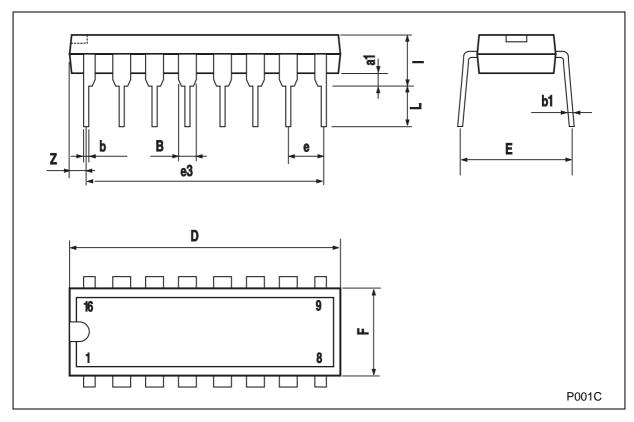
TEST CIRCUIT



 C_L = 50pF or equivalent (includes jig and probe capacitance) R_L = 200K Ω R_T = Z_{OUT} of pulse generator (typically 50 Ω)

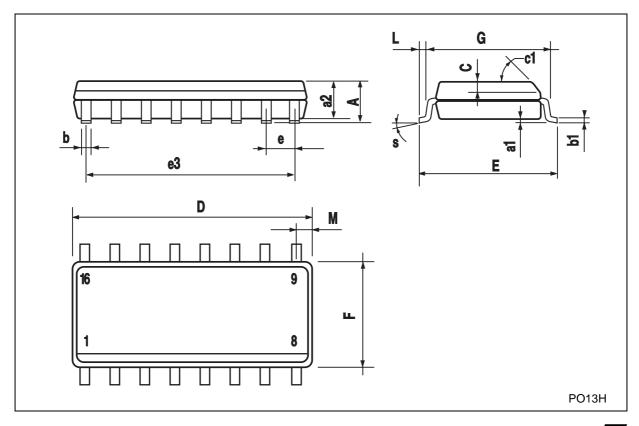
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM		mm.			inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



SO-16 MECHANICAL DATA

DIM		mm.		inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α			1.75			0.068	
a1	0.1		0.2	0.003		0.007	
a2			1.65			0.064	
b	0.35		0.46	0.013		0.018	
b1	0.19		0.25	0.007		0.010	
С		0.5			0.019		
c1			45°	(typ.)	•		
D	9.8		10	0.385		0.393	
E	5.8		6.2	0.228		0.244	
е		1.27			0.050		
еЗ		8.89			0.350		
F	3.8		4.0	0.149		0.157	
G	4.6		5.3	0.181		0.208	
L	0.5		1.27	0.019		0.050	
М			0.62			0.024	
S			8° (max.)	·		



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